Abstracts

Discontinuity effects on high frequency transistors

M.A. Megahed and S.M. El-Ghazaly. "Discontinuity effects on high frequency transistors." 1997 MTT-S International Microwave Symposium Digest 2. (1997 Vol. II [MWSYM]): 609-612.

The effects of input and output discontinuities on high frequency GaAs MESFET performance are analyzed. The transistor circuit, including both the active and passive elements, is evaluated using full-wave three dimensional physically based model. The S-parameters are simulated for different circuit topologies. Results clearly shows that the effect of these discontinuities is significant.

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